

VDS	RDS(on)	ID@25°C
1200V	75mΩ	33A

Applications:

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- EV Charging
- Motor Drives

Features:

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness

Benefits:

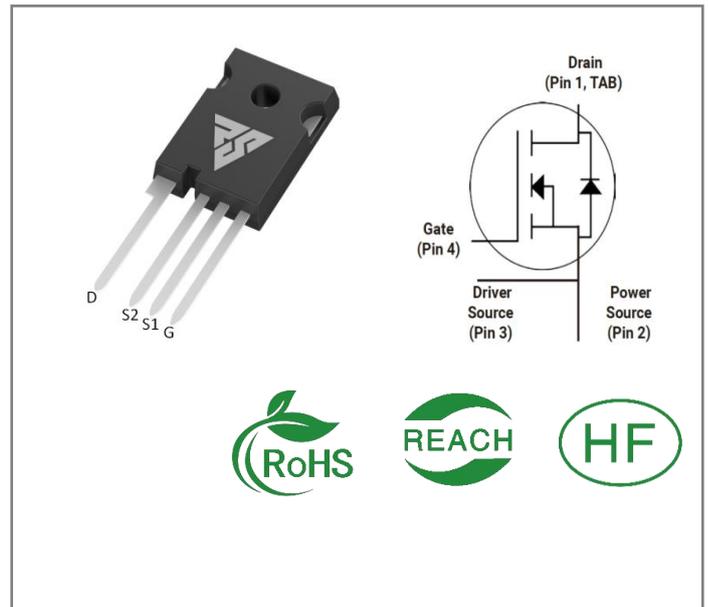
- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSM120075Z	TO-247-4	RSM120075Z	Tube	30 PCS

Maximum Ratings (T_J= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VDSmax	Drain - Source Voltage	1200	V	VGS=0V, ID =100μA	
VGSmax	Gate - Source Voltage	-8/+22	V	Absolute maximum values	
VGSop	Gate - Source Voltage	-4/+18	V	Recommended operational values	
ID	Continuous Drain Current	33 23.8	A	VGS=18V, TC =25°C VGS=18V, TC =100°C	
ID(pulse)	Pulsed Drain Current	80	A	Pulse width tp limited by TJmax	
PD	Power Dissipation	136	W	TC =25°C, TJ =175°C	
TL	Solder Temperature	260	°C		
TJ, Tstg	Operating Junction and Storage Temperature	-55 to + 175	°C		



Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V(BR)DSS	Drain-Source Breakdown Voltage	1200			V	VGS=0V, ID = 100μA	
VGS(th)	Gate Threshold Voltage	1.9	2.6	4.0	V	VGS = VDS, IDS = 5mA, TC = 25°C	
			1.8		V	VGS = VDS, IDS = 5mA, TC = 175°C	
IDSS	Zero Gate Voltage Drain Current		1	100	μA	VDS = 1200V, VGS = 0V	
IGSS+	Gate-Source Leakage Current		10	250	nA	VGS = 22V, VDS = 0V	
IGSS-	Gate-Source Leakage Current		10	250	nA	VGS = -8V, VDS = 0V	
RDS(on)	Drain-Source on-state Resistance		75	95	mΩ	VGS = 18V, ID = 20A, TC = 25°C	
			120			VGS = 18V, ID = 20A, TC = 175°C	
Ciss	Input Capacitance		1200		pF	VGS = 0V, VDS = 1000 V, f = 1MHz, VAC = 25 mV	
Coss	Output Capacitance		63				
Crss	Reverse Transfer Capacitance		9.8				
EON	Turn-On Switching Energy		586		μJ	VDS = 800V, VGS = -4/18V, ID = 20A, RG(ext) = 2.5Ω, L = 100μH	
EOFF	Turn-Off Energy		273				
td(on)	Turn-On Delay Time		13		ns	VDS = 800V, VGS = -4/18 V, ID = 20A, RG(ext) = 2.5 Ω, RL = 20Ω	
tr	Rise Time		12				
td(off)	Turn-Off Delay Time		16				
tf	Fall Time		10				
RG(int)	Internal Gate Resistance		5.5		Ω	f = 1 MHz, VAC = 25mV	
Qgs	Gate to Source Charge		21.5		nC	VDS = 800V, VGS = -4/18V, ID = 20A	
Qgd	Gate to Drain Charge		14.6		nC		
Qg	Total Gate Charge		68.1				

Reverse Diode Characteristics (T_J= 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Max	Unit	Test Conditions	Note
VSD	Diode Forward Voltage	4.2		V	VGS=-4V, ISD =10 A, TJ = 25°C	
		3.8		V	VGS=-4V, ISD=10 A, TJ= 175°C	
IS	Continuous Diode Forward Current		33	A	VGS=-4V,TC= 25°C	
trr	Reverse Recovery time	28		ns	ISD= 20A, VR = 800V	
Qrr	Reverse Recovery Charge	62		nC		
Irrm	Peak Reverse Recovery Current	3.7		A		

Thermal Characteristics (T_J= 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
RθJC	Thermal Resistance from Junction to Case	0.84	°C/W		
RθJA	Thermal Resistance From Junction to Ambient	40			

Typical Feature Curve

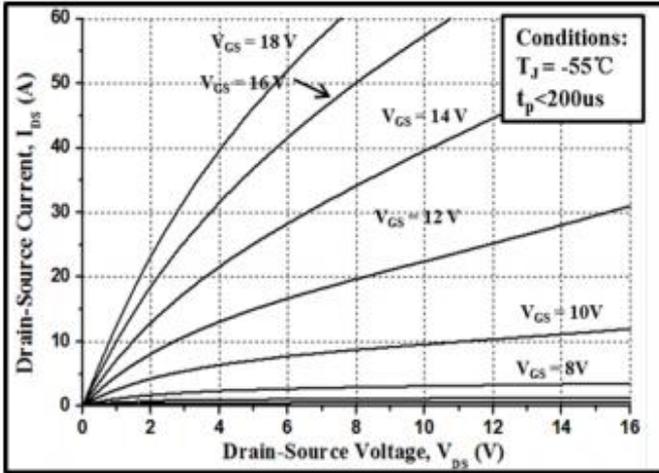


Figure 1. Output Characteristics $T_j = -55^\circ\text{C}$

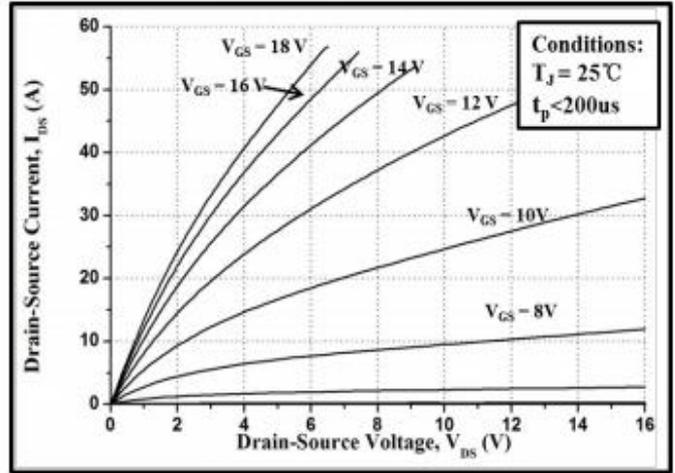


Figure 2. Output Characteristics $T_j = 25^\circ\text{C}$

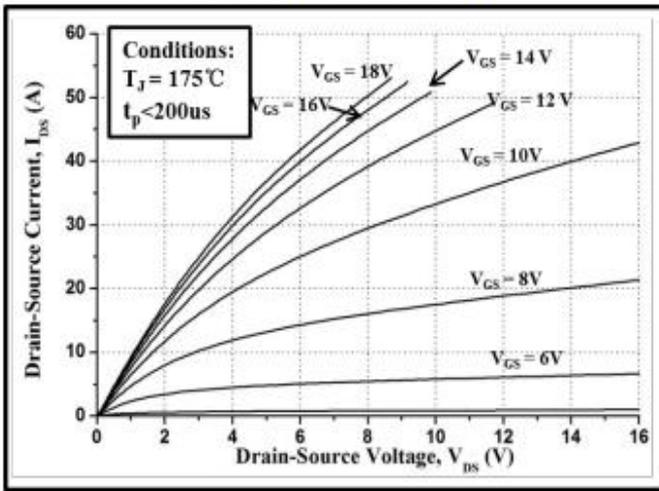


Figure 3. Output Characteristics $T_j = 175^\circ\text{C}$

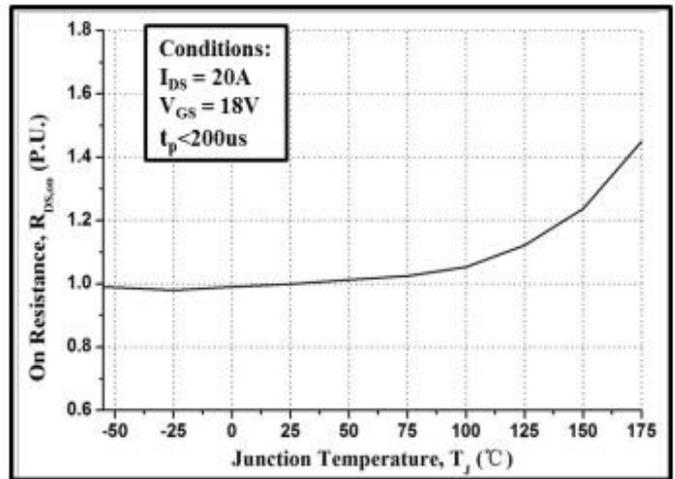


Figure 4. Normalized On-Resistance vs. Temperature

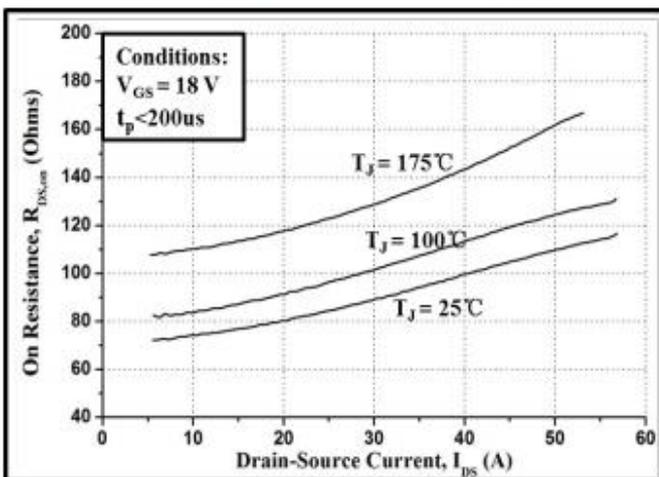


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

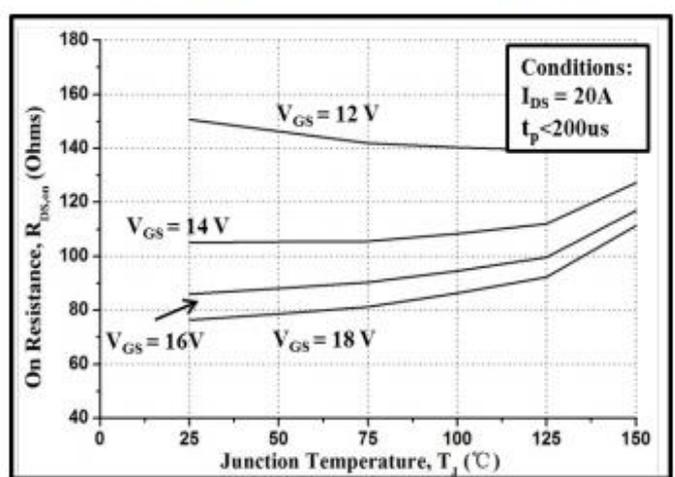


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

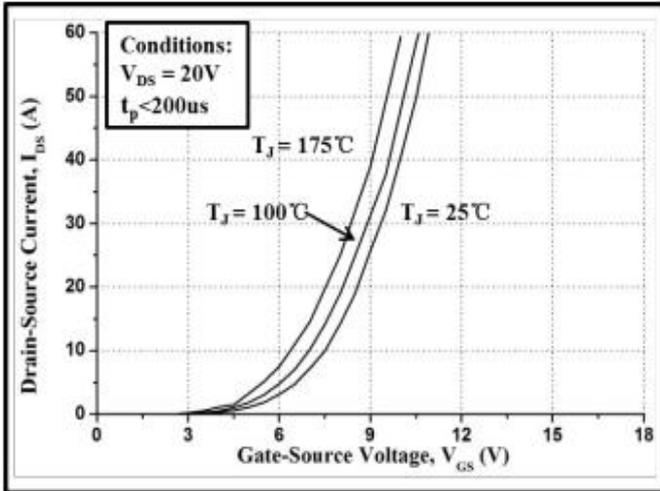


Figure 7. Transfer Characteristic for Various Junction Temperatures

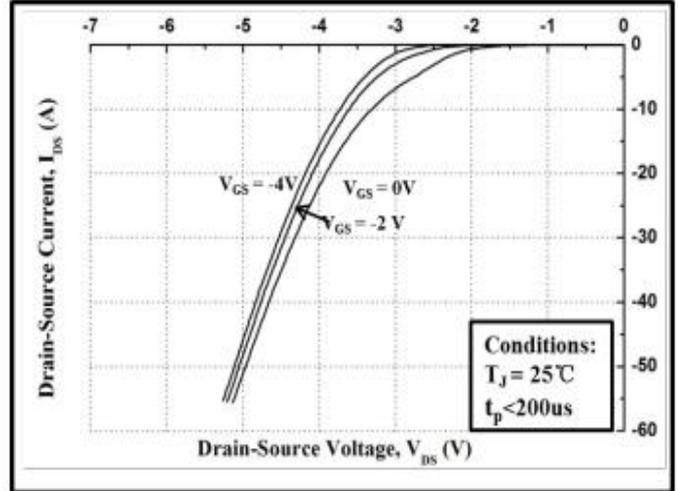


Figure 8. Body Diode Characteristic at 25°C

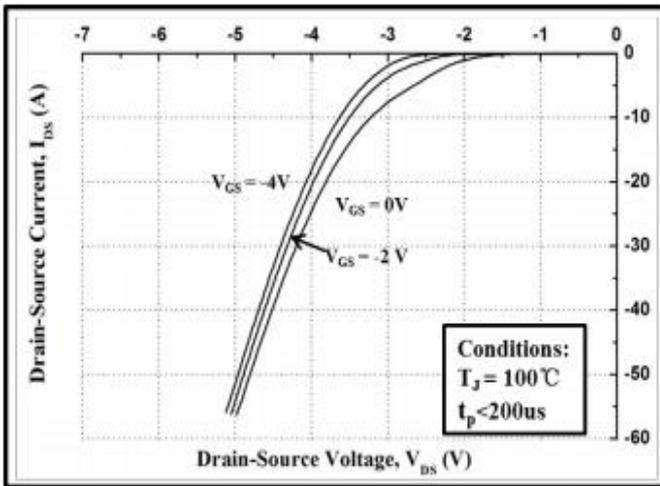


Figure 9. Body Diode Characteristic at 100°C

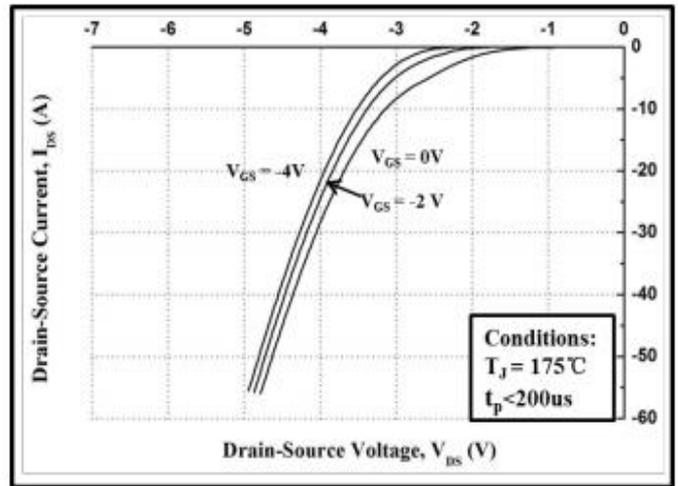


Figure 10. Body Diode Characteristic at 175°C

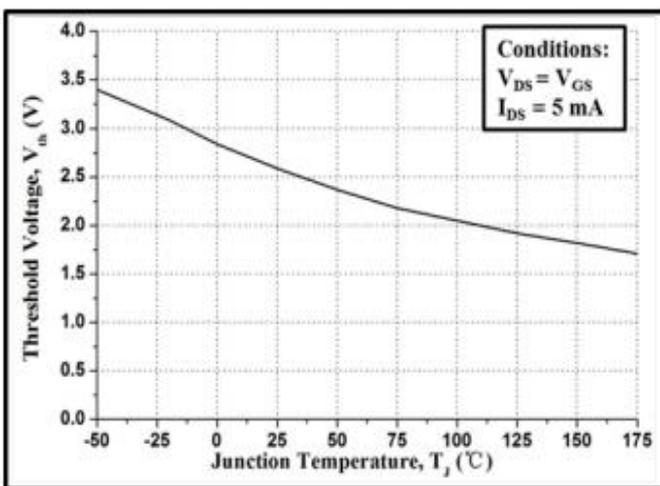


Figure 11. Threshold Voltage vs. Temperature

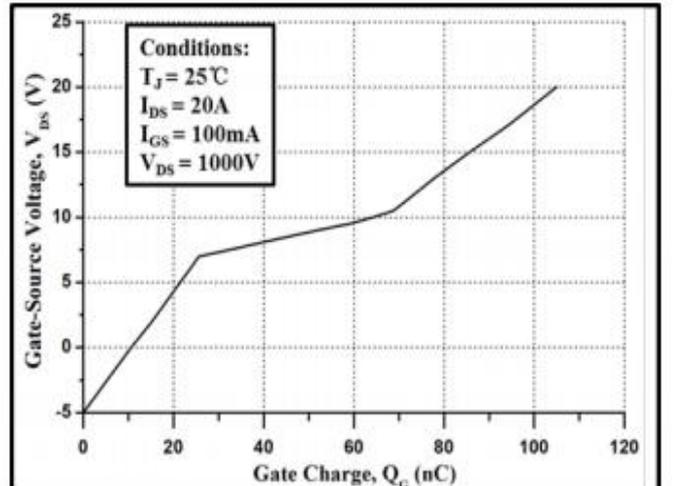


Figure 12. Gate Charge Characteristics

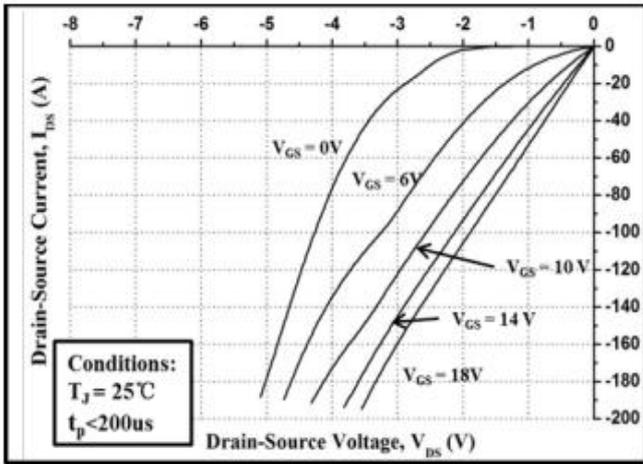


Figure 13. 3rd Quadrant Characteristic at 25°C

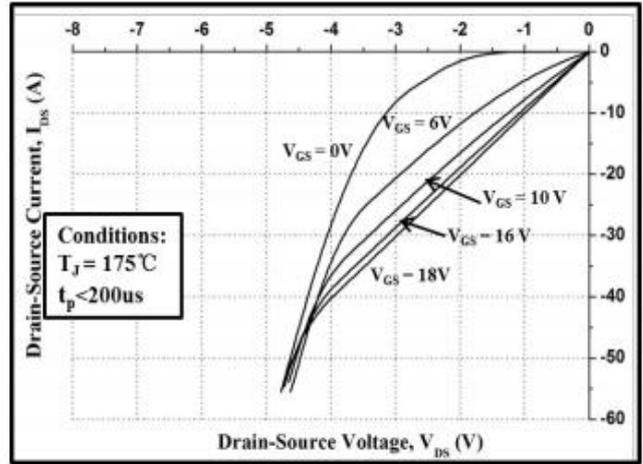


Figure 14. 3rd Quadrant Characteristic at 175°C

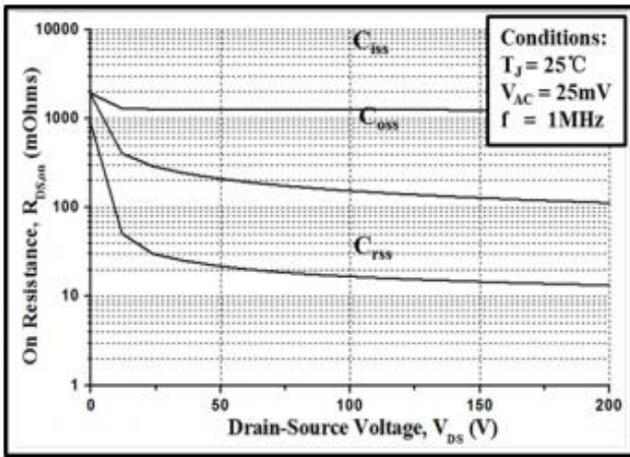


Figure 15. Capacitances vs. Drain-Source Voltage (0 - 200V)

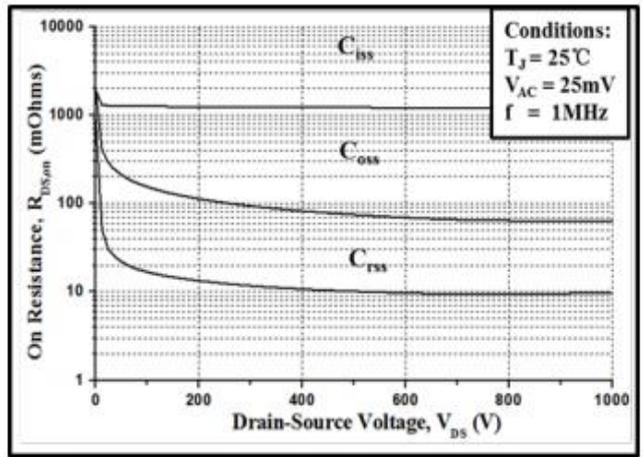
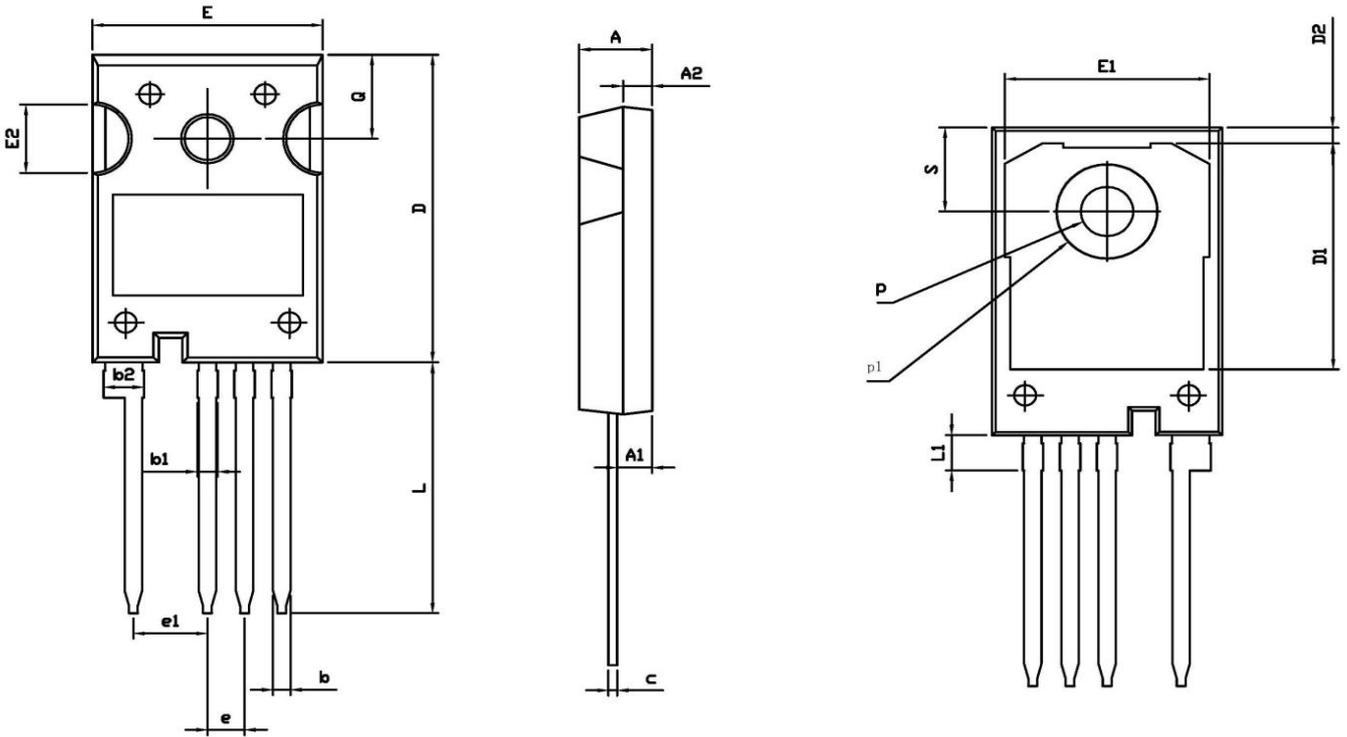
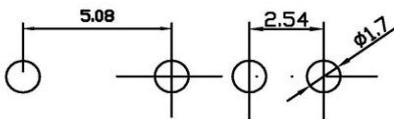


Figure 16. Capacitances vs. Drain-Source Voltage (0 - 1000V)

Package outline drawing(TO-247-4 Unit: mm)



RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.25	2.40	2.45
A2	1.85	2.00	2.15
b	1.05	1.20	1.35
b1	1.00	1.30	1.60
b2	2.35	2.65	2.95
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.50	17.00
D2	0.97	1.17	1.37
e	2.34	2.54	2.74
e1	4.88	5.08	5.28
E	15.60	15.80	16.00
E1	13.50	14.00	14.50
E2	4.80	5.00	5.20
L	18.08	18.38	18.68
L1	2.38	2.58	2.78
p	3.50	3.60	3.70
p1	6.60	6.80	7.00
Q	6.00	6.15	6.30
S	6.00	6.15	6.30

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